

**ROCHESTER INSTITUTE OF TECHNOLOGY
MICROELECTRONIC ENGINEERING**

Basic Analog Electronic Circuits

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Microelectronic Engineering

Rochester Institute of Technology

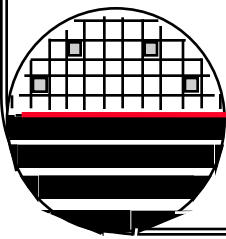
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MicroE webpage: <http://www.microe.rit.edu>



OUTLINE

Introduction

Op Amp

Comparator

Bistable Multivibrator

RC Oscillator

RC Integrator

Peak Detector

Switched Capacitor Amplifier

Capacitors

Design Examples

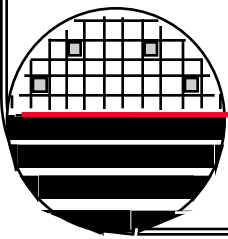
References

Homework

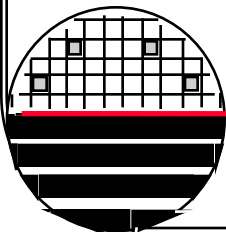
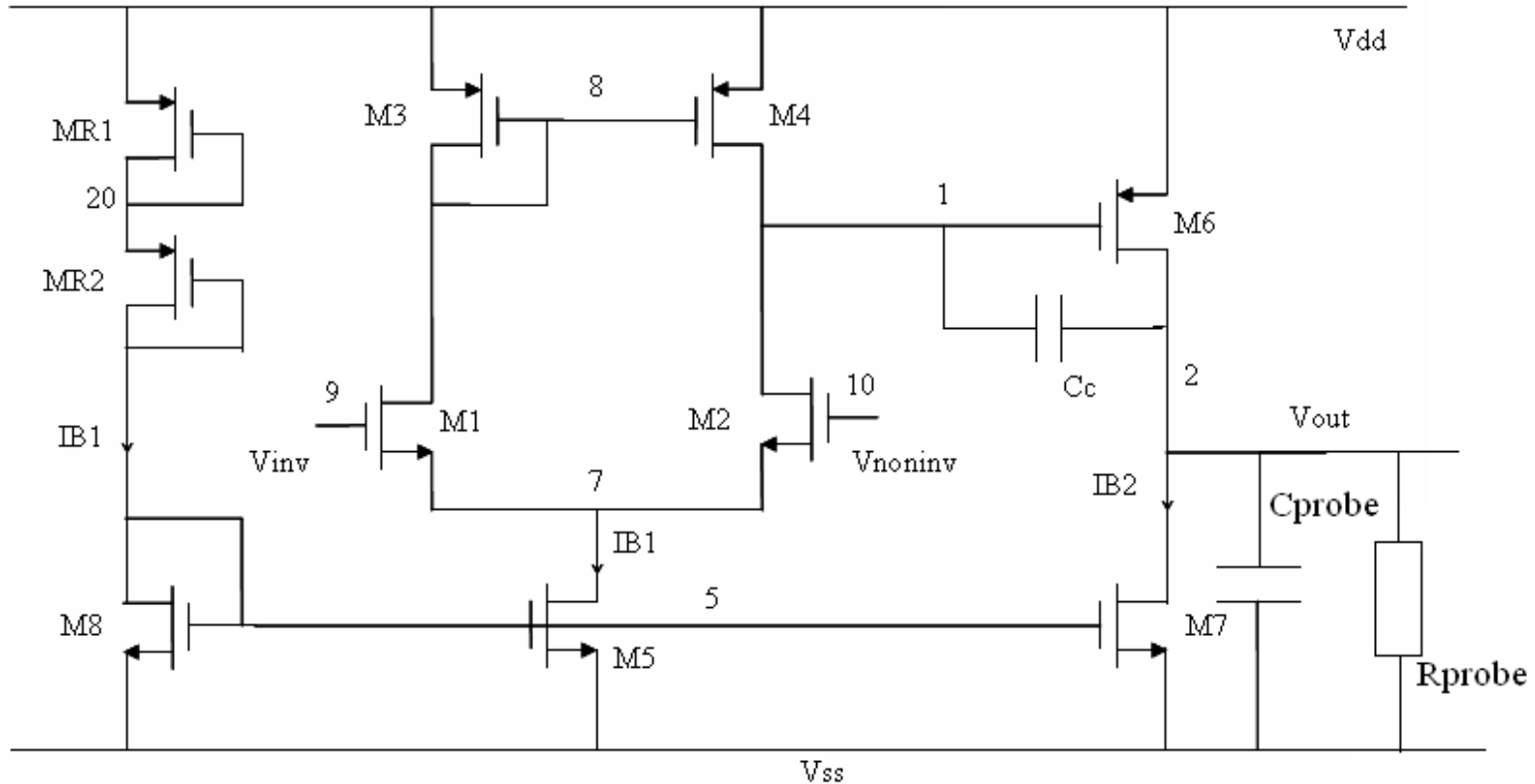
INTRODUCTION

Analog electronic circuits are different from digital circuits in that the signals are expected to have any value rather than two discrete values. **Primitive** analog components include the diode, mosfet, BJT, resistor, capacitor, etc,. Analog circuit **building blocks** include single stage amplifiers, differential amplifiers, constant current sources, voltage references, etc. **Basic** analog electronic circuits include the operational amplifier, inverting amplifier, non-inverting amplifier, integrator, bistable multivibrator, peak detector, comparator, RC oscillator, etc. **Mixed-mode** analog integrated circuits include D-to-A, A-to-D, etc.

This document will introduce some **Basic** analog electronic circuits.

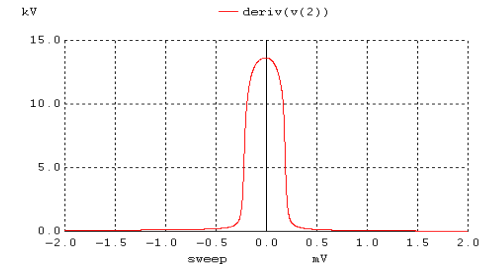


BASIC TWO STAGE OPERATIONAL AMPLIFIER



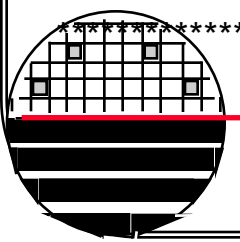
SPICE ANALYSIS OF OP AMP VERSION 2

```
.incl rit_sub_param.txt
m1 8 9 7 6 cmosn w=9u l=5u nrd=1 nrs=1 ad=45p pd=28u as=45p ps=28u
m2 1 10 7 6 cmosn w=9u l=5u nrd=1 nrs=1 ad=45p pd=28u as=45p ps=28u
m3 8 8 4 4 cmosp w=21u l=5u nrd=1 nrs=1 ad=102p pd=50u as=102p
ps=50u
m4 1 8 4 4 cmosp w=21u l=5u nrd=1 nrs=1 ad=102p pd=50u as=102p
ps=50u
m5 7 5 6 6 cmosn w=40u l=5u nrd=1 nrs=1 ad=205p pd=90u as=205p
ps=90u
m6 2 1 4 4 cmosp w=190u l=5u nrd=1 nrs=1 ad=950p pd=400u as=950p
ps=400u
m7 2 5 6 6 cmosn w=190u l=5u nrd=1 nrs=1 ad=950p pd=400u as=950p
ps=400u
m8 5 5 6 6 cmosn w=40u l=5u nrd=1 nrs=1 ad=205p pd=90u as=205p
ps=90u
vdd 4 0 3
vss 6 0 -3
cprobe 2 0 30p
Rprobe 2 0 1meg
cc 1 2 0.6p
mr1 20 20 4 4 cmosp w=6u l=10u nrd=1 nrs=1 ad=200p pd=60u as=200p
ps=60u
mr2 5 5 20 4 cmosp w=6u l=10u nrd=1 nrs=1 ad=200p pd=60u as=200p
ps=60u
*****
```



13.5kV/V gain

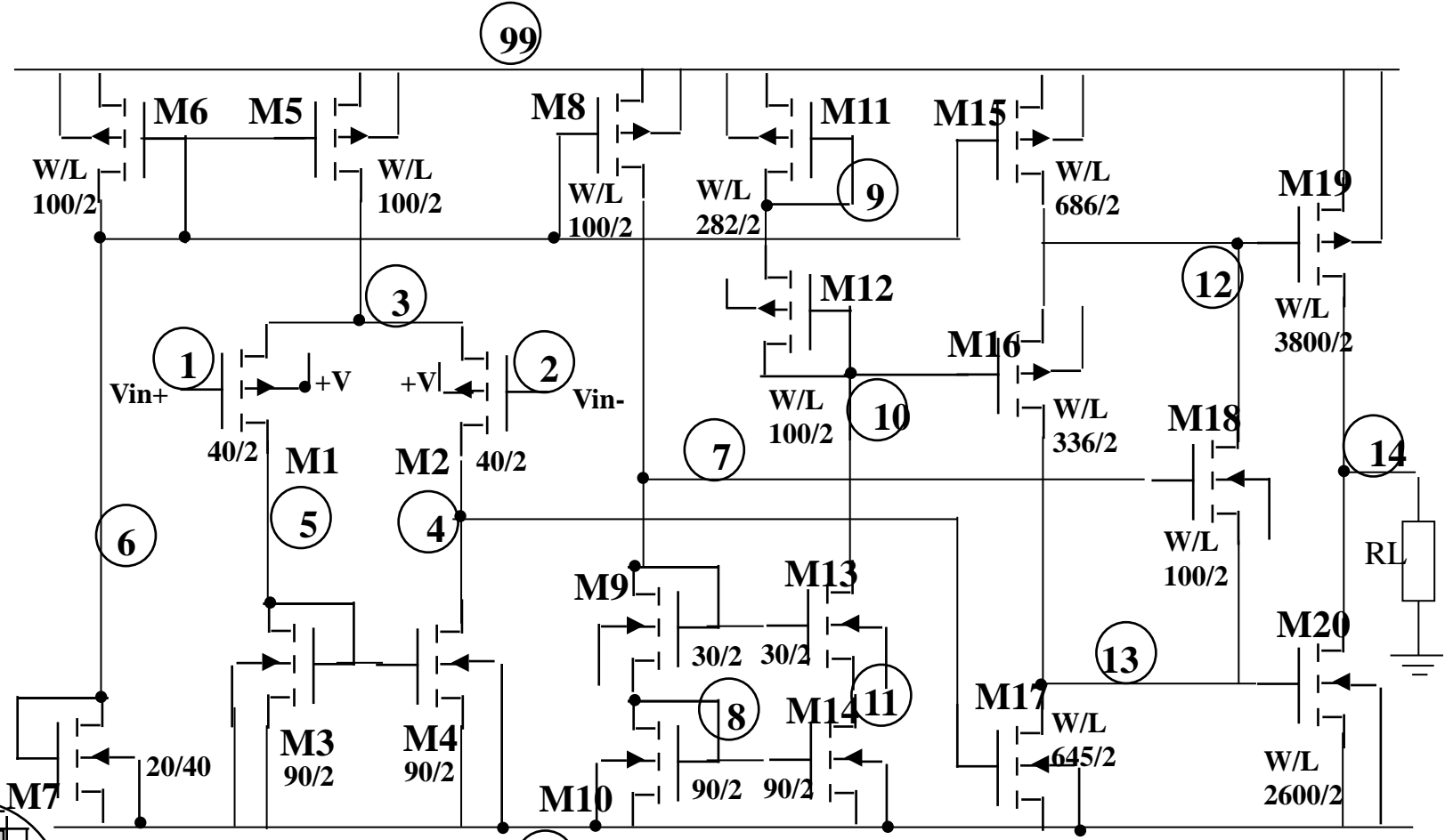
```
*** dc open loop gain *****
vi1 9 0 0
vi2 10 0 0
*.dc vi2 -0.002 0.002 1u
.dc vi2 -1 1 0.1m
***** open loop frequency
characteristics *****
*vi1 9 0 0
*vi2 10 0 dc 0 ac 1u
*.ac dec 100 10 1g
.end
```



OPERATIONAL AMPLIFIER



RIT OP AMP WITH OUTPUT STAGE



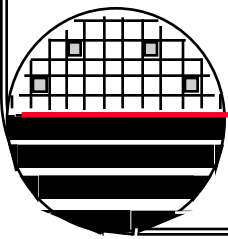
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W/L

OPERATIONAL AMPLIFIERS

The 741 Op Amp is a general purpose bipolar integrated circuit that has input bias current of 80nA, and input voltage of +/- 15 volts @ supply maximum of +/- 18 volts. The output voltage can not go all the way to the + and - supply voltage. At a minimum supply of +/- 5 volts the output voltage can go ~6 volts p-p.

The newer Op Amps have rail-rail output swing and supply voltages as low as +/- 1.5 volts. The MOSFET input bias currents are ~ 1pA. The NJU7031 is an example of this type of Op Amp.



LOW VOLTAGE, RAIL-TO-RAIL OP AMP



NJU7031/32/34

LOW VOLTAGE C-MOS OPERATIONAL AMPLIFIER

■ GENERAL DESCRIPTION

The NJU7031/32/34 are single, dual and quad single supply, low offset, output full swing C-MOS Operational Amplifiers.

The wide operating voltage 3V to 16V, High slew rate 3.5V/μs and output full swing are suitable for fast signal processing amplifiers. Additionally, low input bias current 1pA, and single supply operation offer amplification of the very small signal around the ground level.

The NJU7031 has external offset null function.

■ FEATURES

- High Slew Rate 3.5V/μs
 - Wide Operating Voltage +3V to +16V
 - Output Voltage with full Swing $V_{OM}=9.98V$ typ. (@ $V_{DD}=10V$)
 - Input Common Mode Voltage Range
 $V_{ICM}=0V$ to 9V (@ $V_{DD}=10V$)
 - Low Bias Current $I_B=1pA$ typ.
 - Input Common Mode Voltage range includes ground.
 - External Offset Null Adjustment (Only NJU7031)
 - C-MOS Technology
 - Package Outline
- NJU7031 (single) DIP8, DMP8, SSOP8
 NJU7032 (dual) DIP8, DMP8
 NJU7034 (quad) DIP14, DMP14, SSOP14

■ PACKAGE OUTLINE



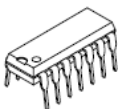
NJM7031D
NJU7032D



NJM7031M
NJU7032M



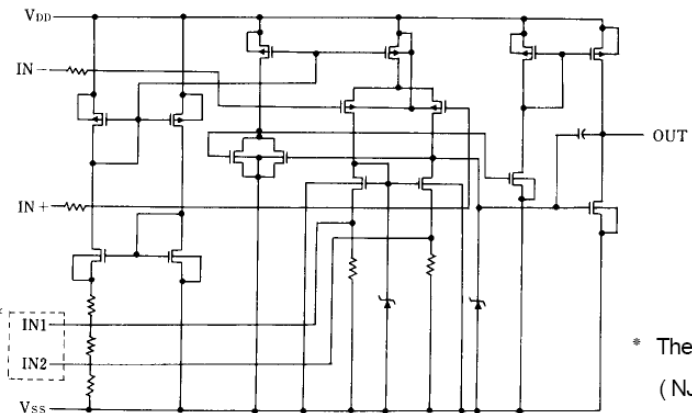
NJM7031V



NJM7034D

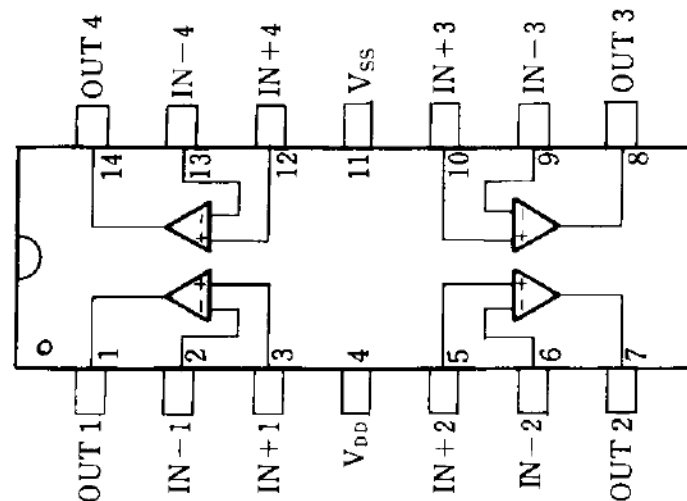


NJM7034M



* The (NJ

New Japan Radio Co., Ltd

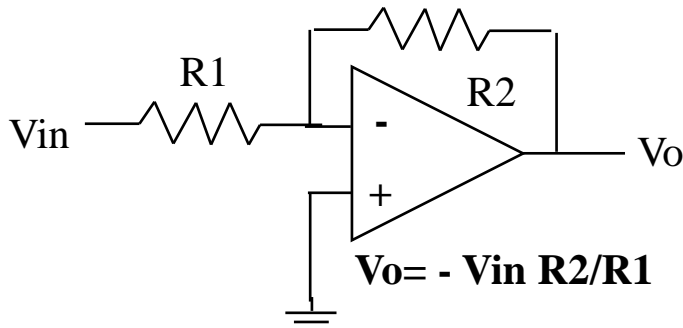


NJU7034D

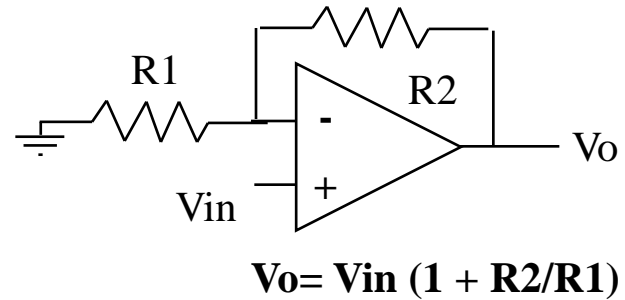
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Microelectronic Engineering*

SOME BASIC ANALOG ELECTRONIC CIRCUITS

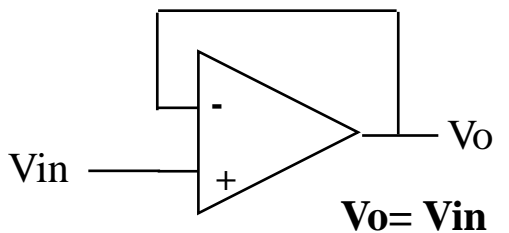
These circuits should be familiar:



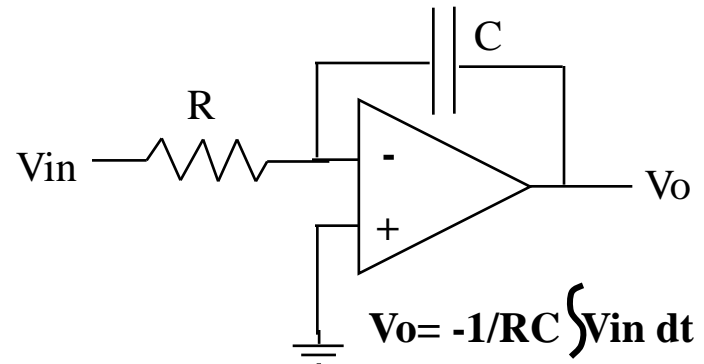
Inverting Amplifier



Non-Inverting Amplifier

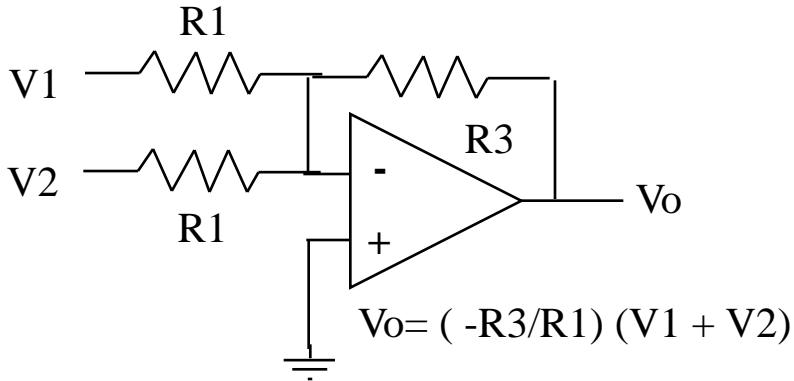


Unity Gain Buffer

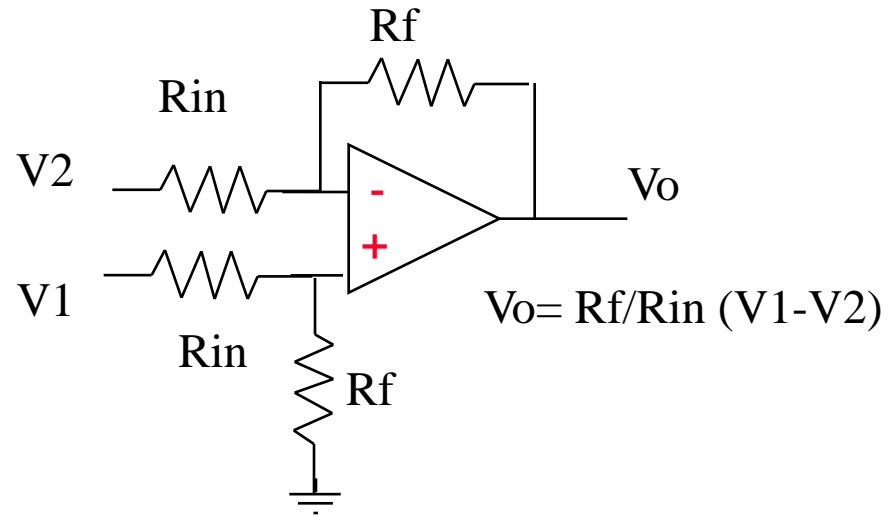


Integrator

SOME BASIC ANALOG ELECTRONIC CIRCUITS

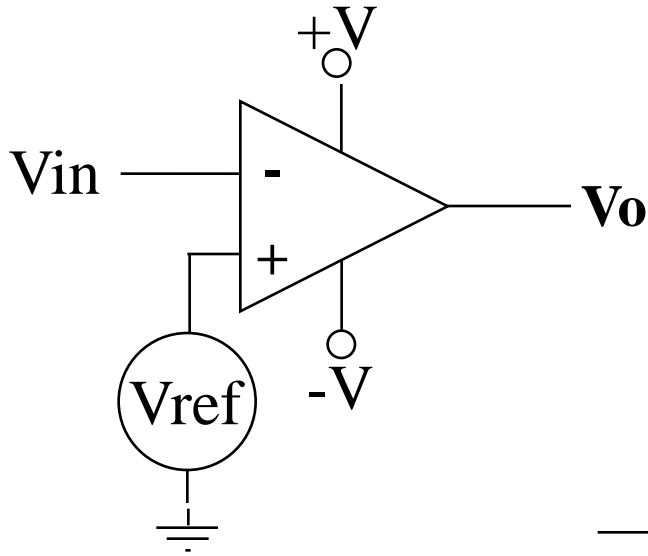


Inverting Summer

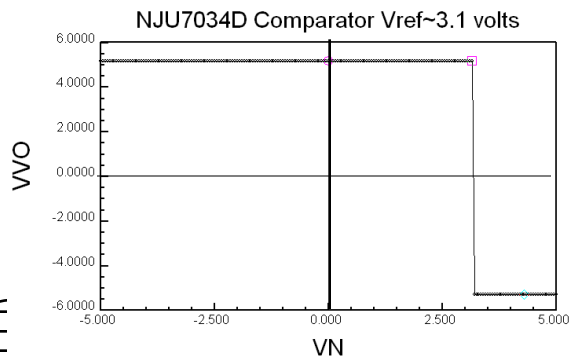
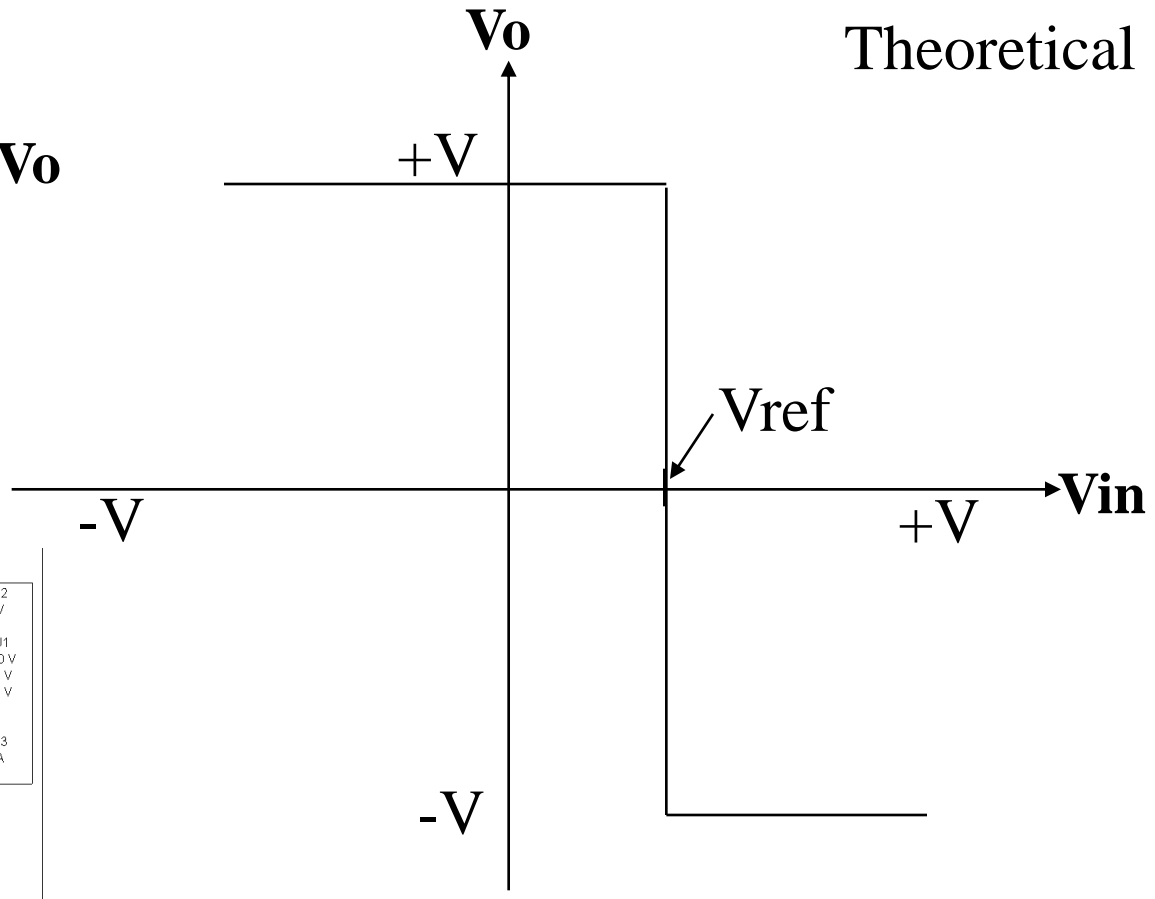


Difference Amplifier

COMPARATOR



Theoretical

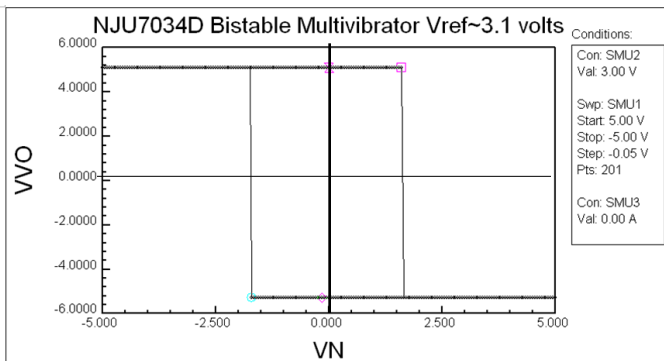
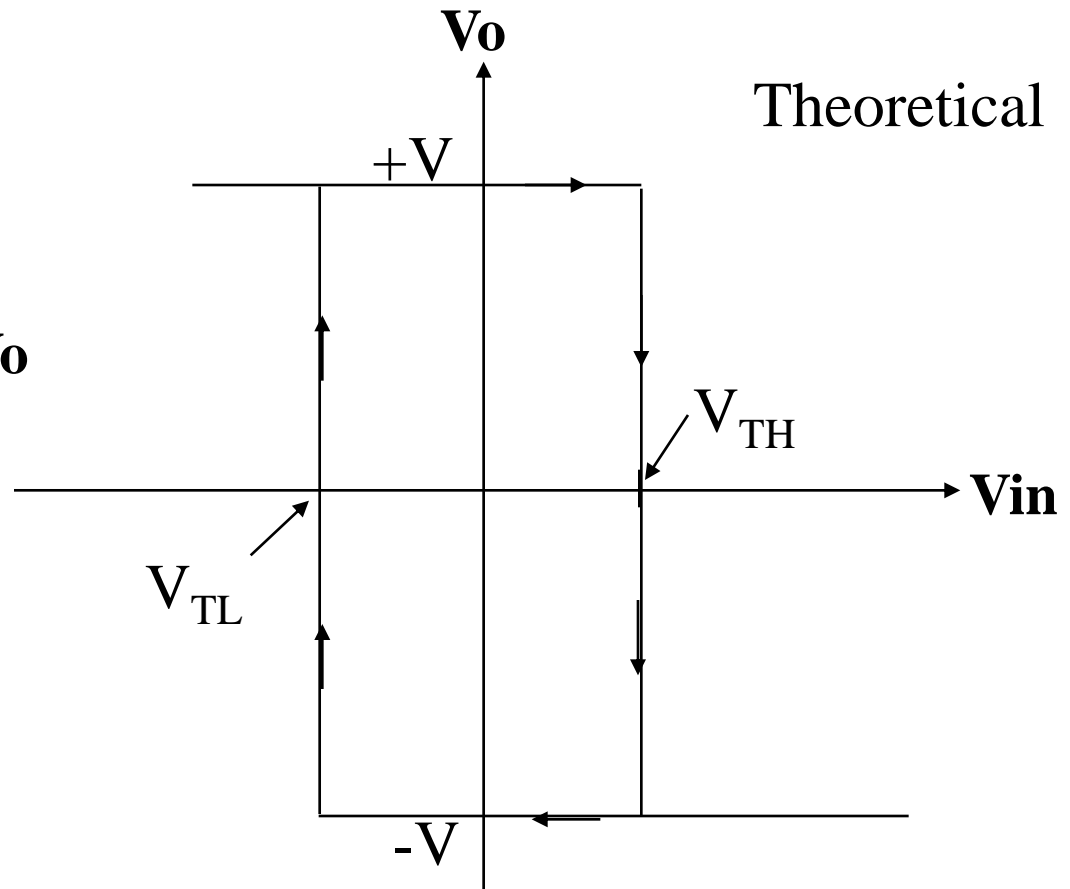
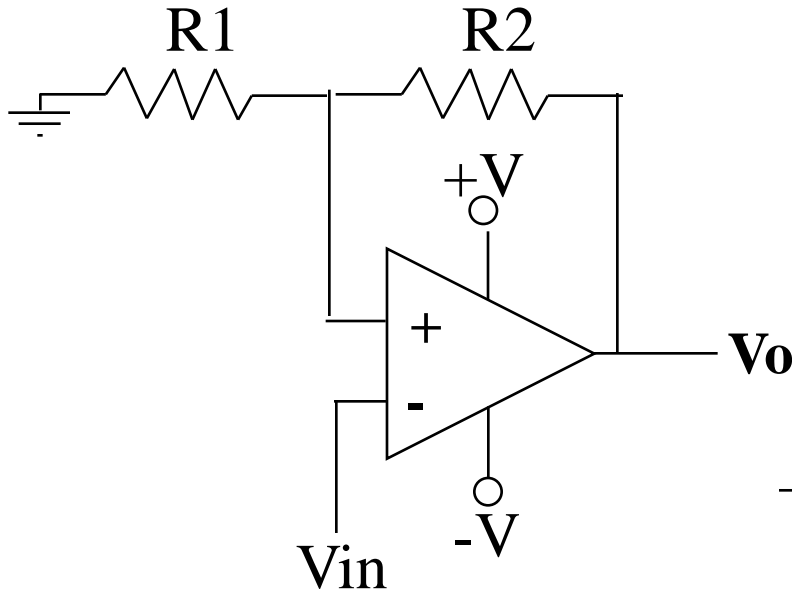


Conditions:
 Con: SMU2
 Val: 3.00 V
 Swp: SMU1
 Start: -5.00 V
 Stop: 5.00 V
 Step: 0.05 V
 Pts: 201
 Con: SMU3
 Val: 0.00 A

Measured

Fit #1:	Fit #2:	Cursors: X	Y
None	None	3.15	5.15
****	****	4.30	-5.30
****	****	0.00	5.15

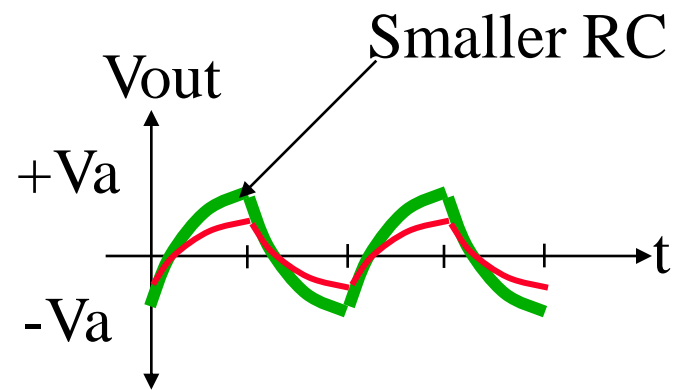
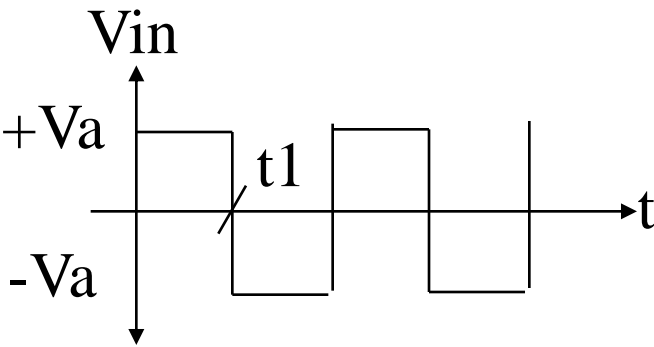
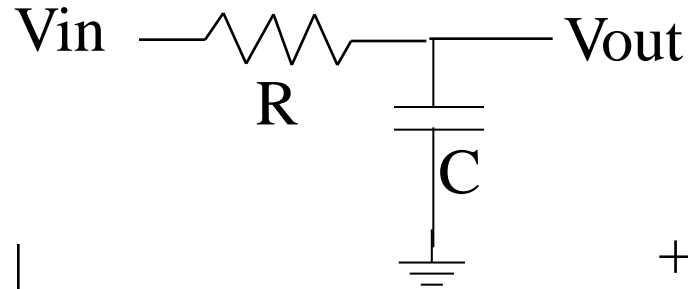
BISTABLE CIRCUIT WITH HYSTERESIS



Measured

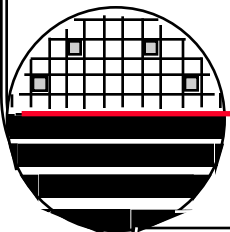
Sedra and Smith pg 1187

RC INTEGRATOR

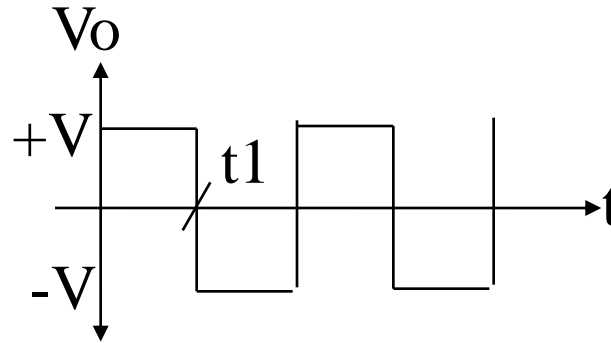
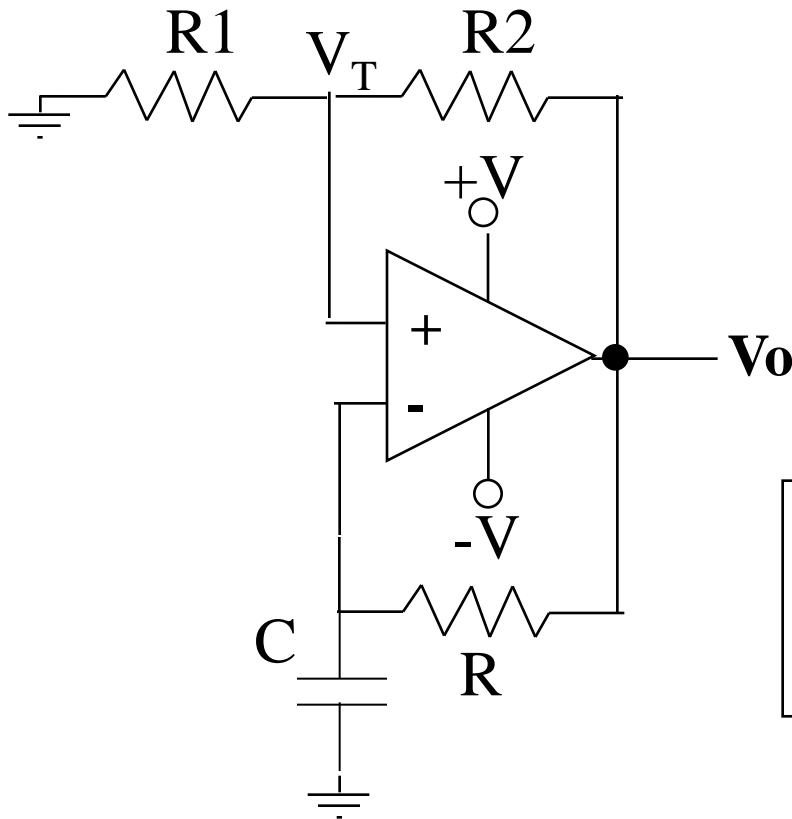


$$V_{out} = (-V_a) + [2V_a(1 - e^{-t/RC})] \quad \text{for } 0 < t < t_1$$

If $R=1\text{MEG}$ and $C=10\text{pF}$ find $RC=10\text{us}$
 so t_1 might be $\sim 20\text{us}$



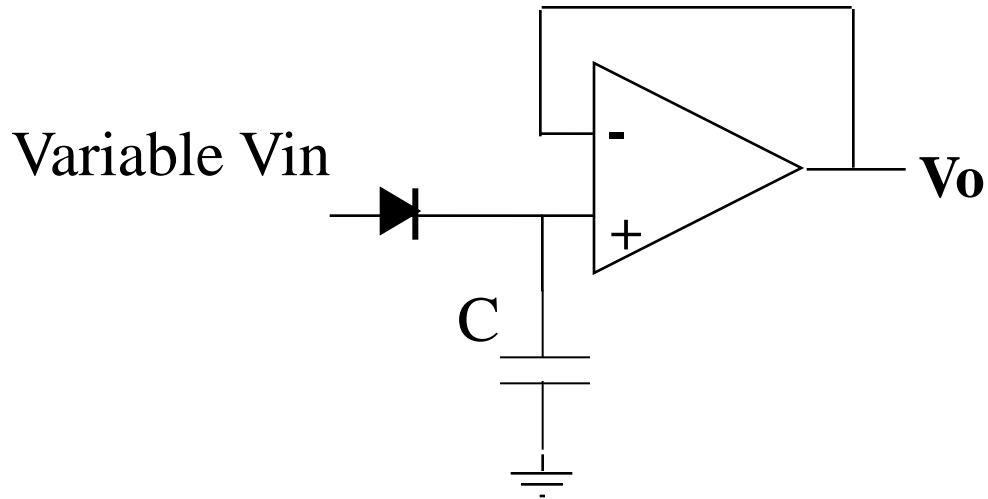
OSCILLATOR (MULTIVIBRATOR)



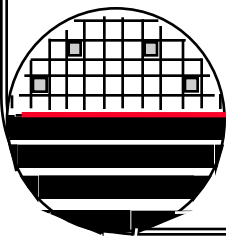
$$\text{Period} = T = 2RC \ln \left(\frac{1 + V_T/V}{1 - V_T/V} \right)$$

Bistable Circuit with Hysteresis and RC Integrator

PEAK DETECTOR



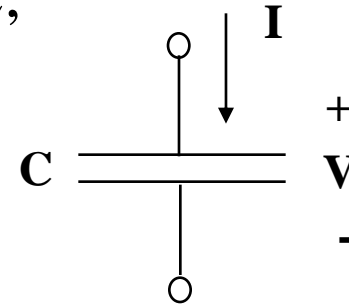
Diode reverse leakage current $\sim 100\text{nA}$



CAPACITORS

Capacitor - a two terminal device whose current is proportional to the time rate of change of the applied voltage;

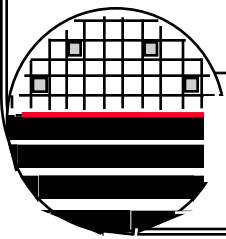
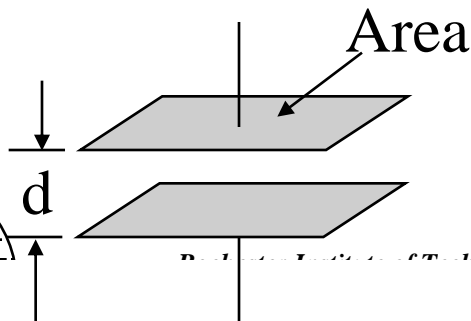
$$I = C \, dV/dt$$



a capacitor C is constructed of any two conductors separated by an insulator. The capacitance of such a structure is:

$$C = \epsilon_0 \epsilon_r \text{Area}/d$$

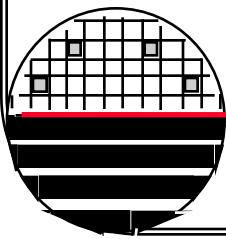
where ϵ_0 is the permittivity of free space
 ϵ_r is the relative permittivity
 Area is the overlap area of the two
 conductor separated by distance d
 $\epsilon_0 = 8.85E-14 \text{ F/cm}$
 $\epsilon_r \text{ air} = 1$
 $\epsilon_r \text{ SiO}_2 = 3.9$



DIELECTRIC CONSTANT OF SELECTED MATERIALS

Vacuum	1
Air	1.00059
Acetone	20
Barium strontium titanate	500
Benzene	2.284
Conjugated Polymers	6 to 100,000
Ethanol	24.3
Glycerin	42.5
Glass	5-10

Methanol	30
Photoresist	3
Plexiglass	3.4
Polyimide	2.8
Rubber	3
Silicon	11.7
Silicon dioxide	3.9
Silicon Nitride	7.5
Teflon	2.1
Water	80-88

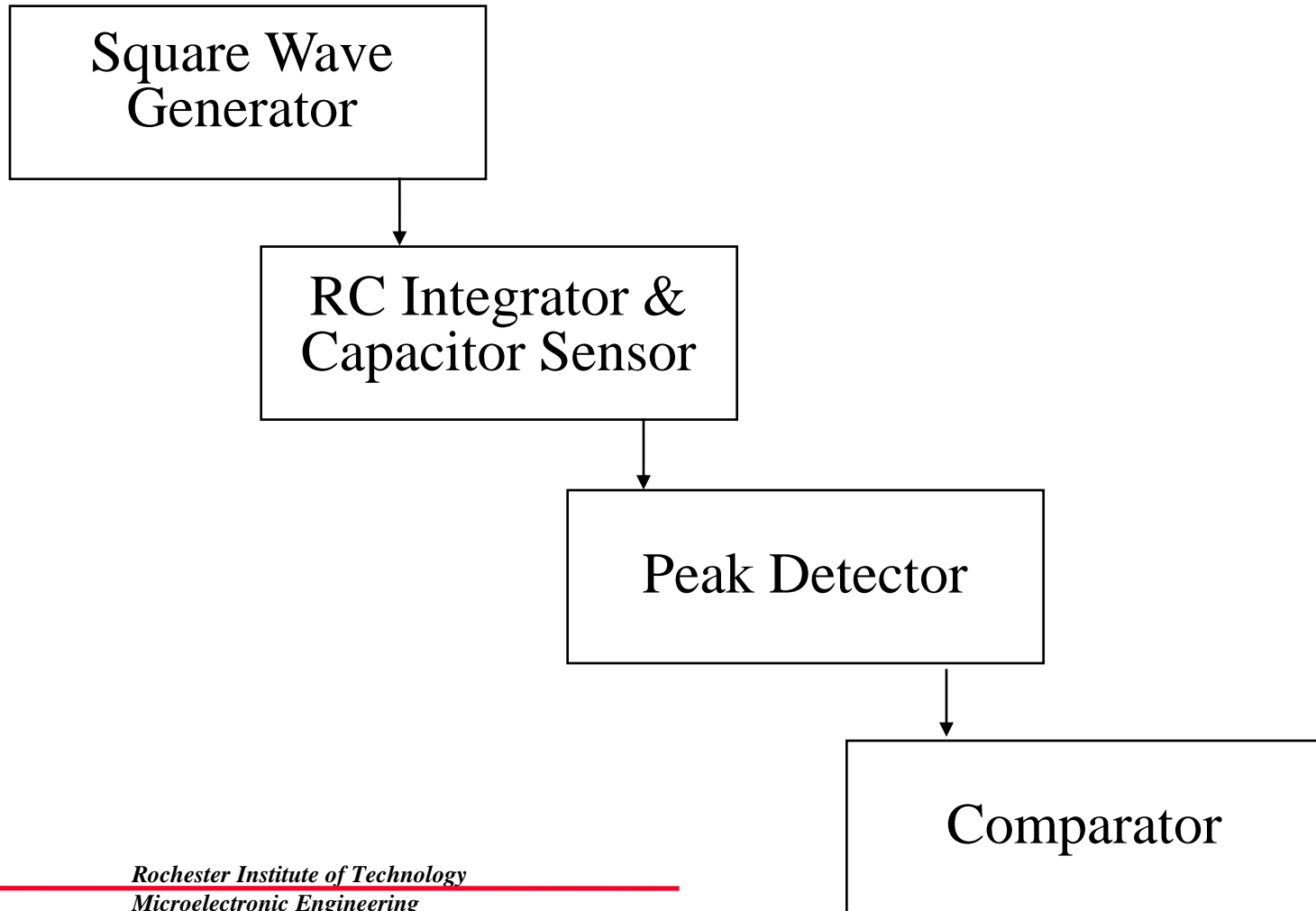


<http://www.asiinstruments.com/technical/Dielectric%20Constants.htm>

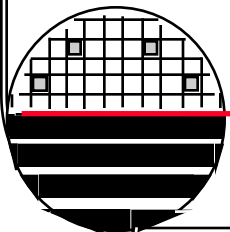
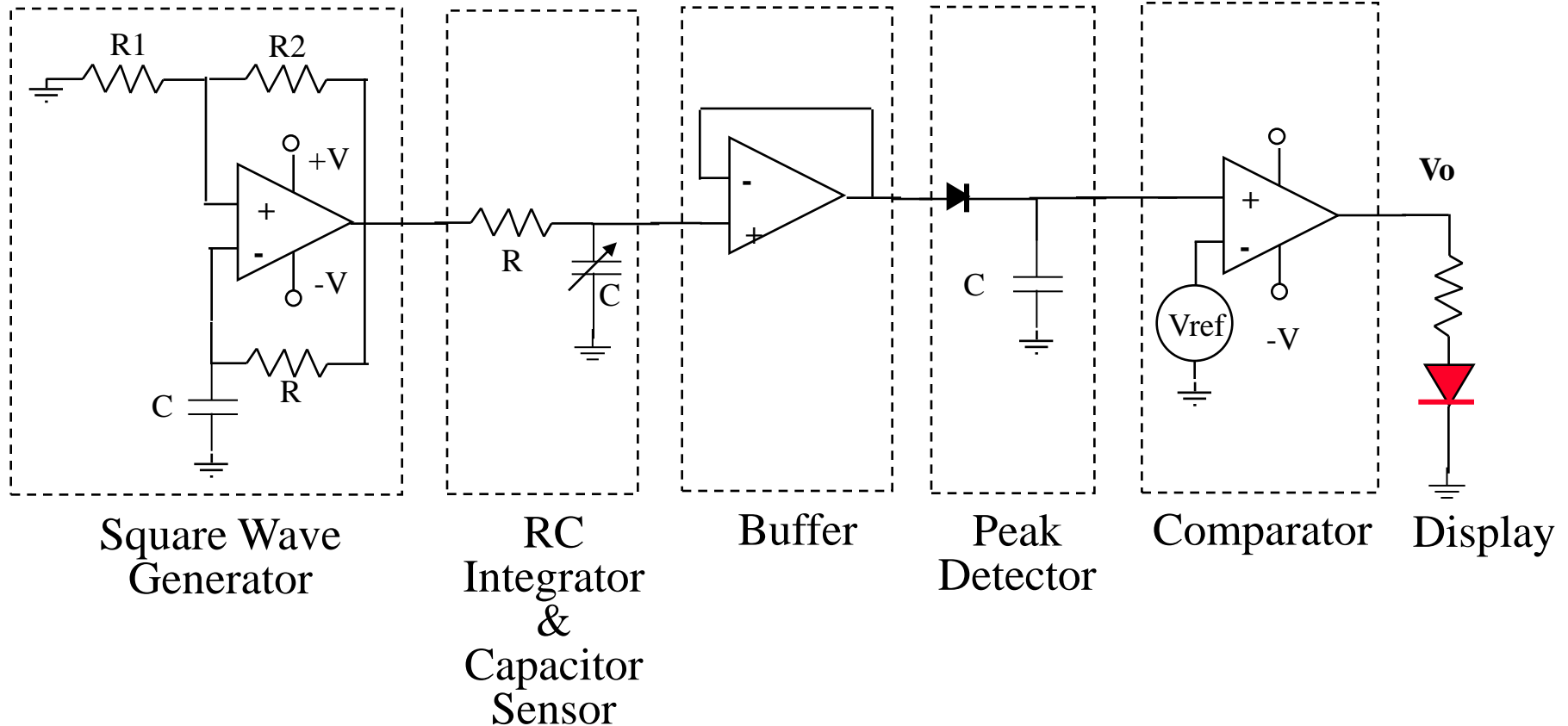
CALCULATIONS

	A	B	C	D	E	F	G	H	I
1	Rochester Institute of Technology								8-Apr-08
2	Dr. Lynn Fuller		Microelectronic Engineering, 82 Lomb Memorial Dr., Rochester, NY 14623						
3									
4	To use this spread sheet enter values in the white boxes. The rest of the sheet is protected and should not be								
5	changed unless you are sure of the consequences. The results are displayed in the purple boxes.								
6									
7	Capacitance of Two Parallel Plates								
8	Capacitance = $\epsilon_0 \epsilon_r \text{Area}/d$					C =	8.85E-12	F	
9				eo = Permittivity of free space			8.85E-14	F/cm	
10				er = relative permittivity =			1		
11					Area =		1.00E-02	cm2	
12				number of pairs of plates, N =			1		
13				distance between plates, d =			1	μm	
14				If round plates, Diameter =			0	μm	
15				If rectangular plates, length =			1000	μm	
16				If rectangular plates, width =			1000	μm	
17	Force Between Two Parallel Plates					Force =	4.43E-04	N	
18	Electrostatic Force= $\epsilon_0 \epsilon_r \text{Area } V^2/2d^2$			Applied Voltage, V =			10	volts	
19									
20	Capacitance for very Thick Interdigitated Fingers								
21		C = (N-1) $\epsilon_0 \epsilon_r L h/s$			Capacitance, C =		1.77E-13	F	
22				Number of Fingers, N =			101		

DESIGN EXAMPLE

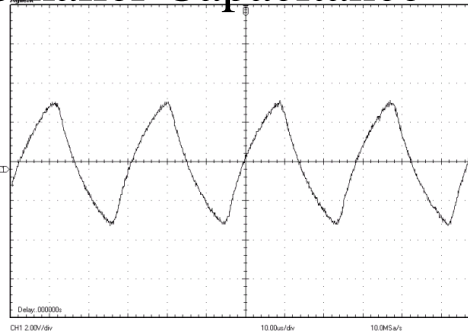


DESIGN EXAMPLE – CAPACITOR SENSOR

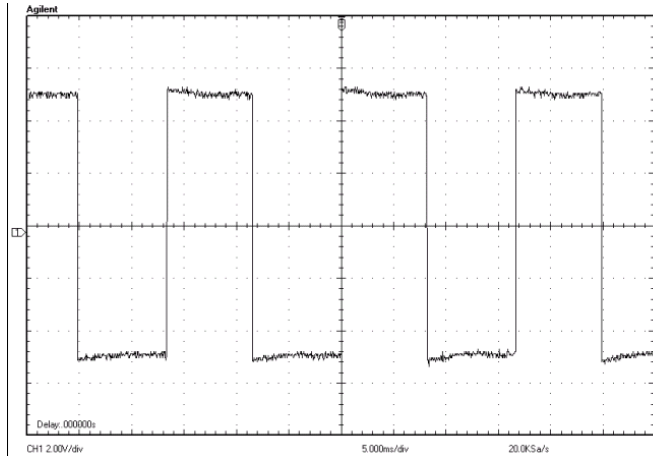
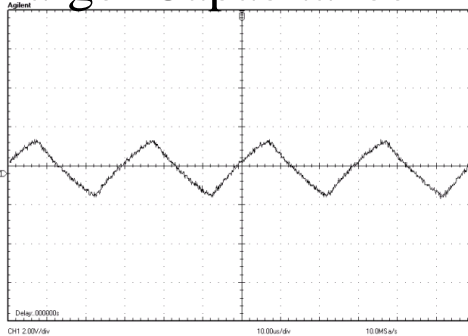


EXAMPLE LABORATORY RESULTS

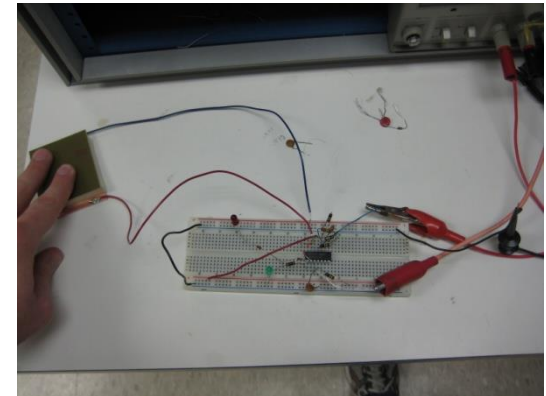
Smaller Capacitance



Larger Capacitance



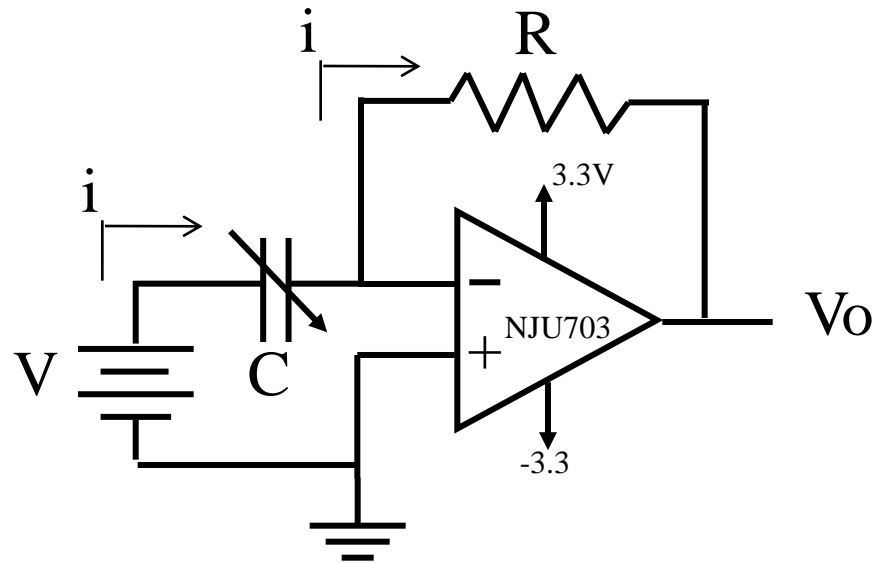
Square Wave Generator Output



Display

Buffer Output

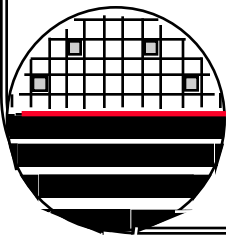
CAPACITOR MICROPHONE PLUS AMPLIFIER



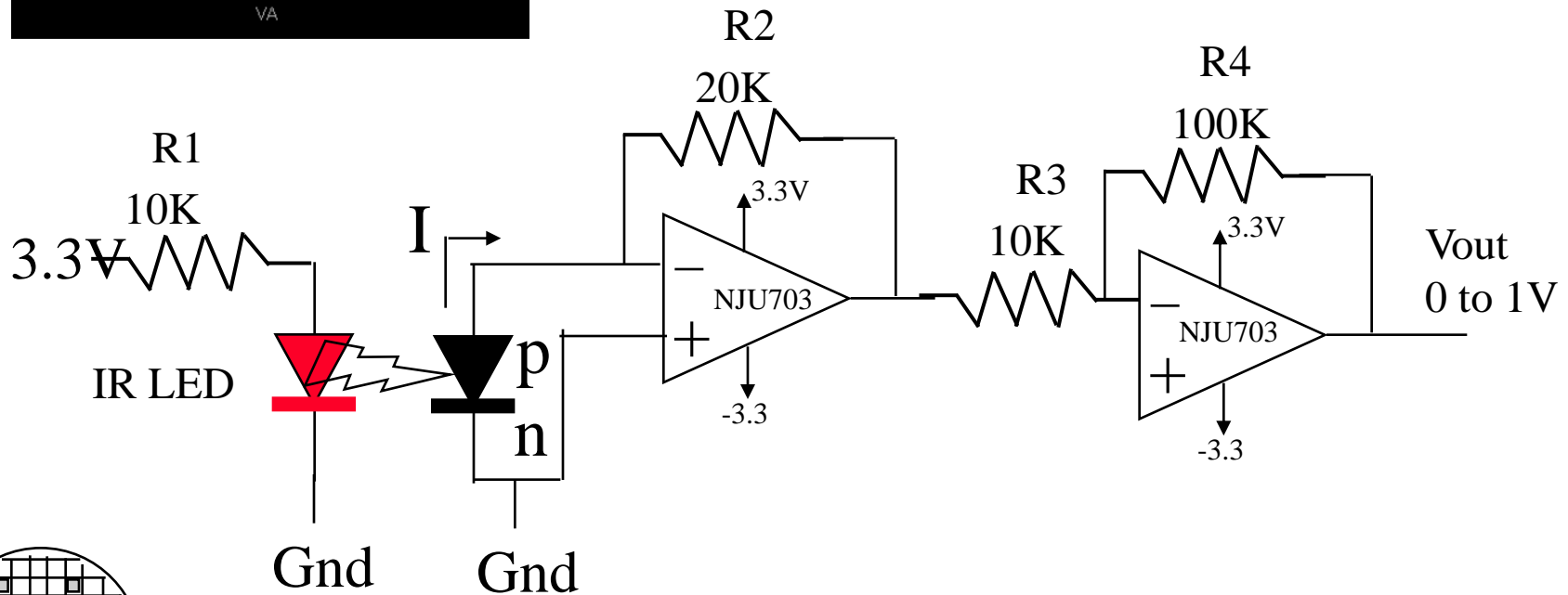
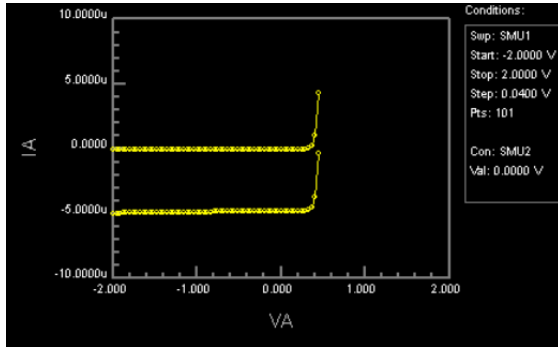
$$V_o = - i R$$

$$i = d(CV)/dt, \quad V \text{ is constant } C = C_o + C_m \sin(2\pi ft)$$

$$i = V C_m 2 \pi f \cos(2\pi ft)$$

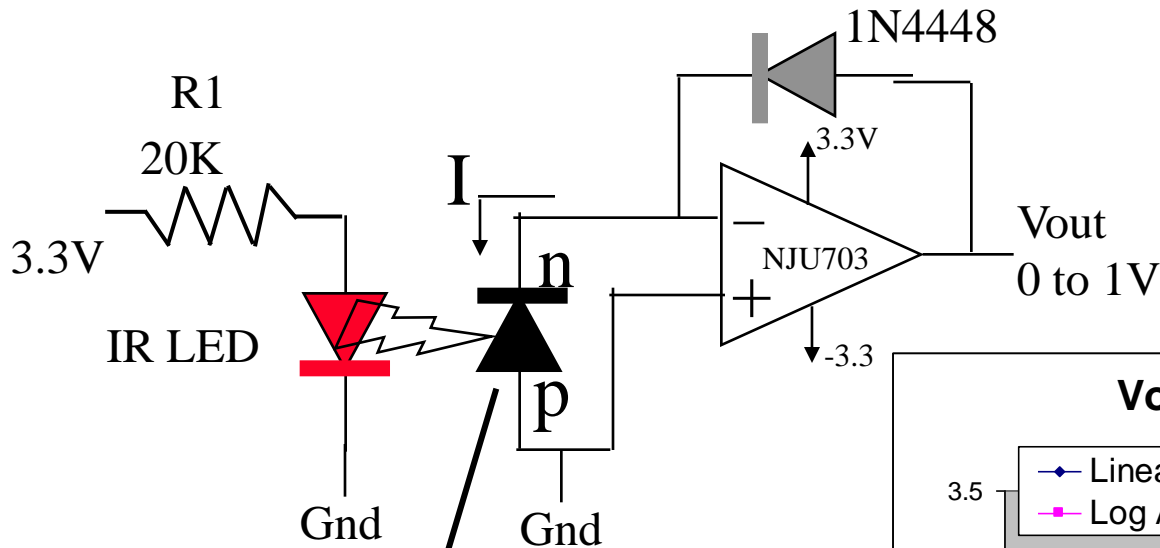


PHOTODIODE I TO V LINEAR AMPLIFIER

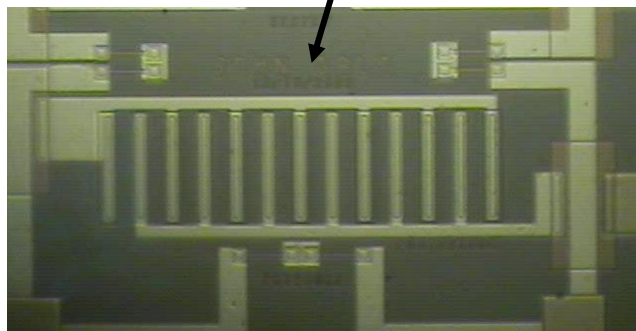


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PHOTO DIODE I TO V LOG AMPLIFIER



Linear amplifier uses 100K ohm in place of the 1N4448



Photodiode

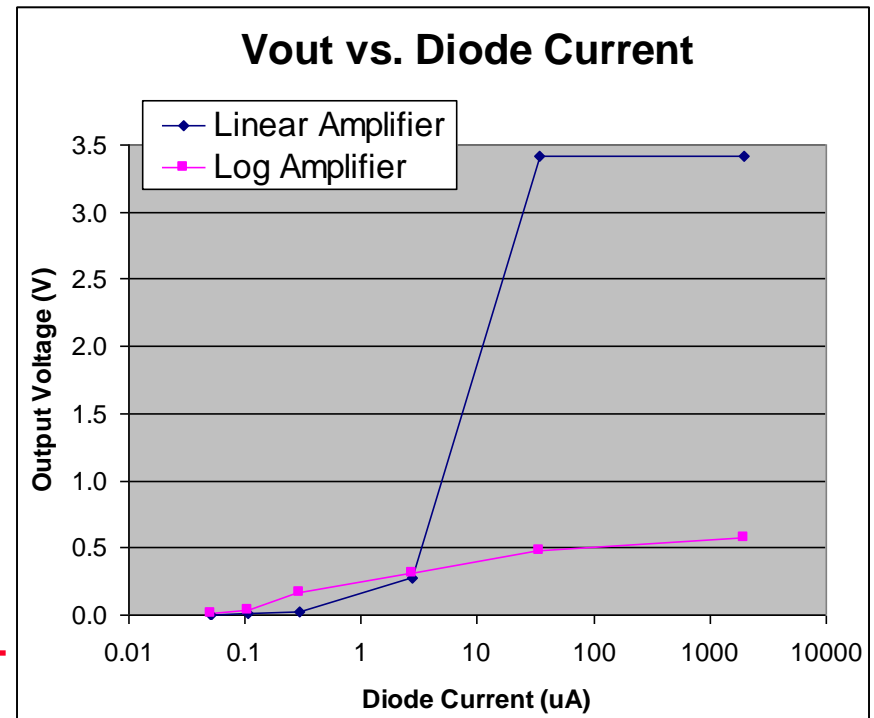
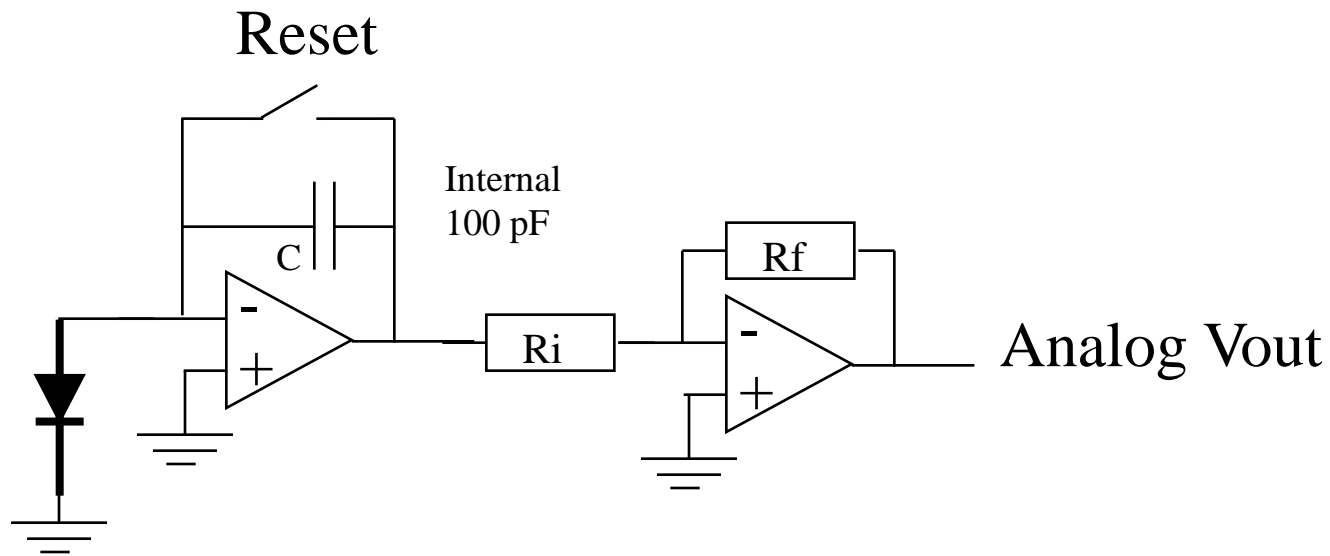
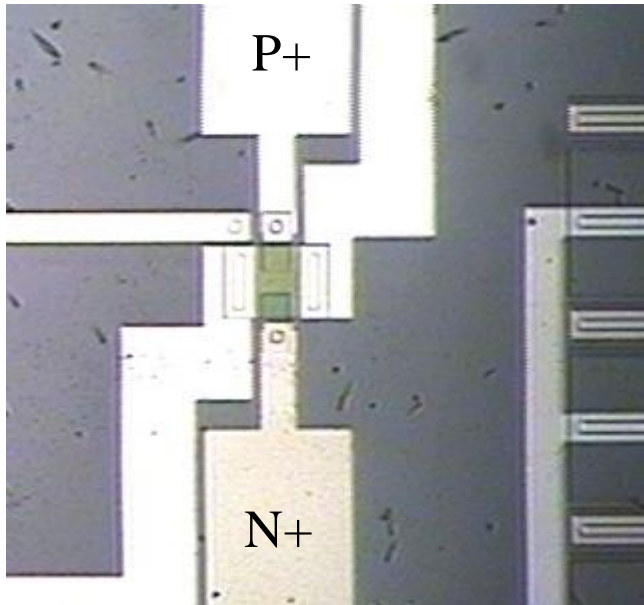


PHOTO DIODE I TO V INTEGRATING AMPLIFIER

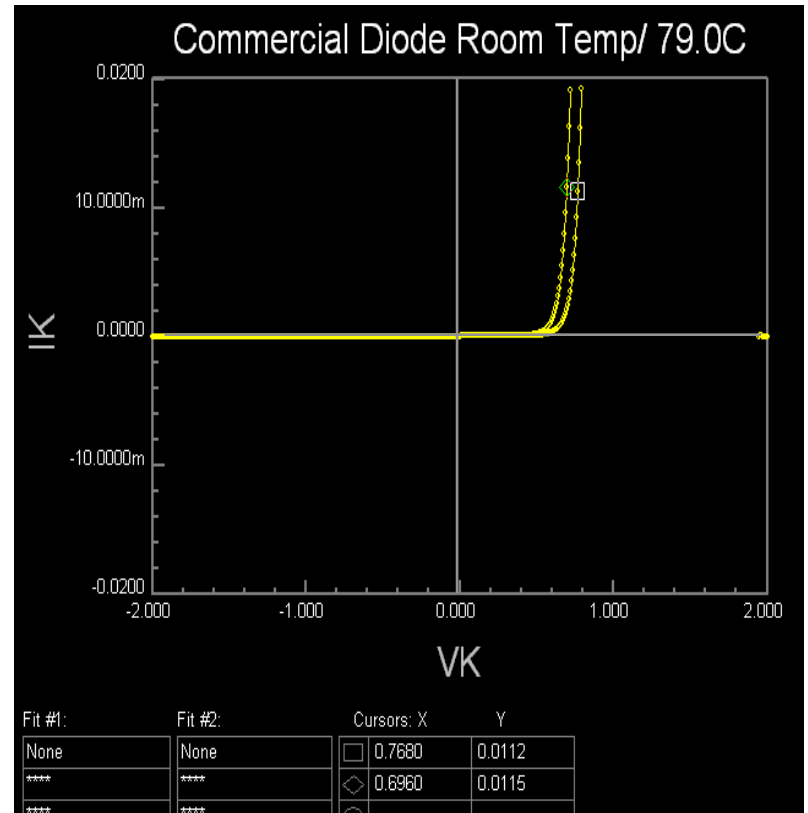


Integrator and amplifier allow for measurement at low light levels

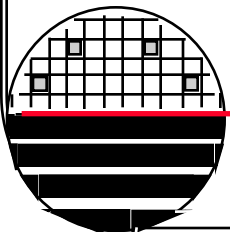
DIODE AS A TEMPERATURE SENSOR



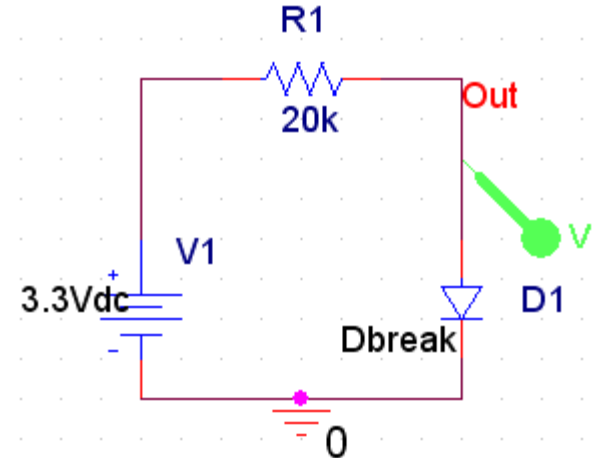
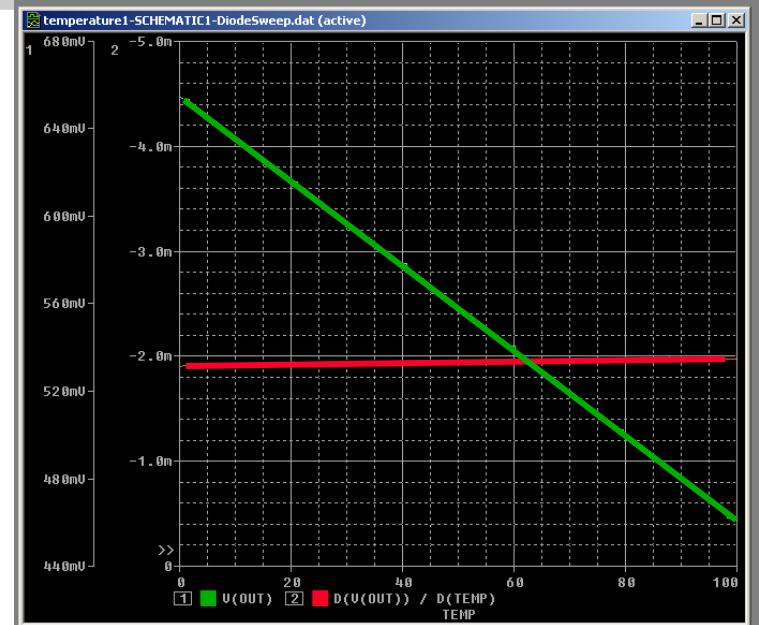
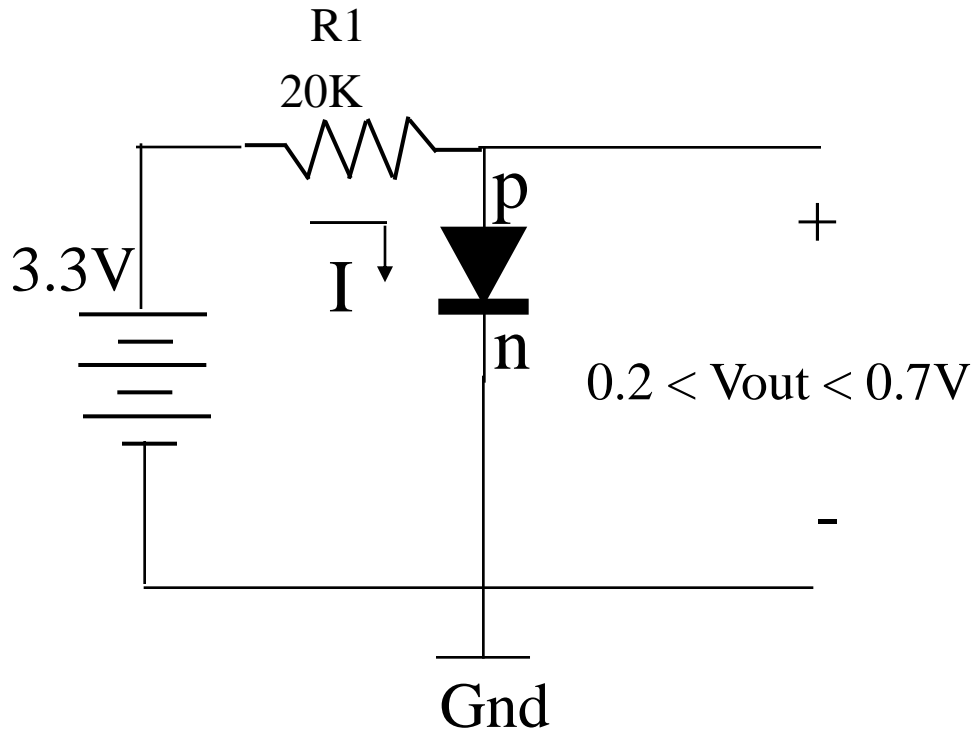
Poly Heater, Buried pn Diode, N+ Poly to Aluminum Thermocouple



Compare with theoretical $-2.2\text{mV}/^\circ\text{C}$

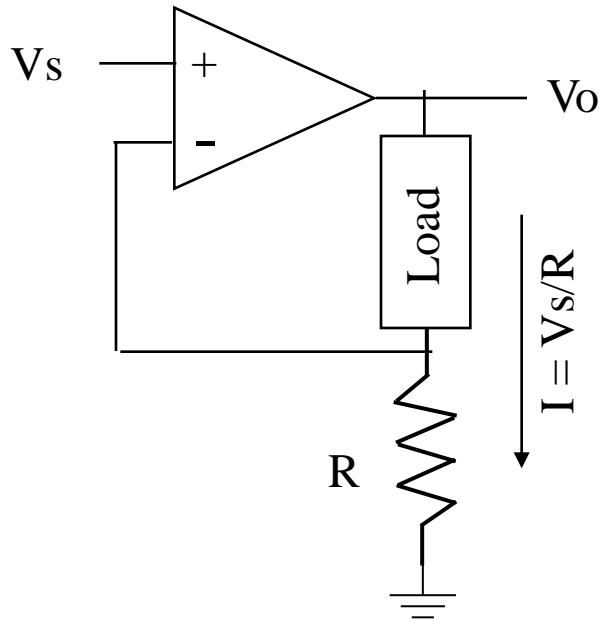


SIGNAL CONDITIONING FOR TEMPERATURE SENSOR

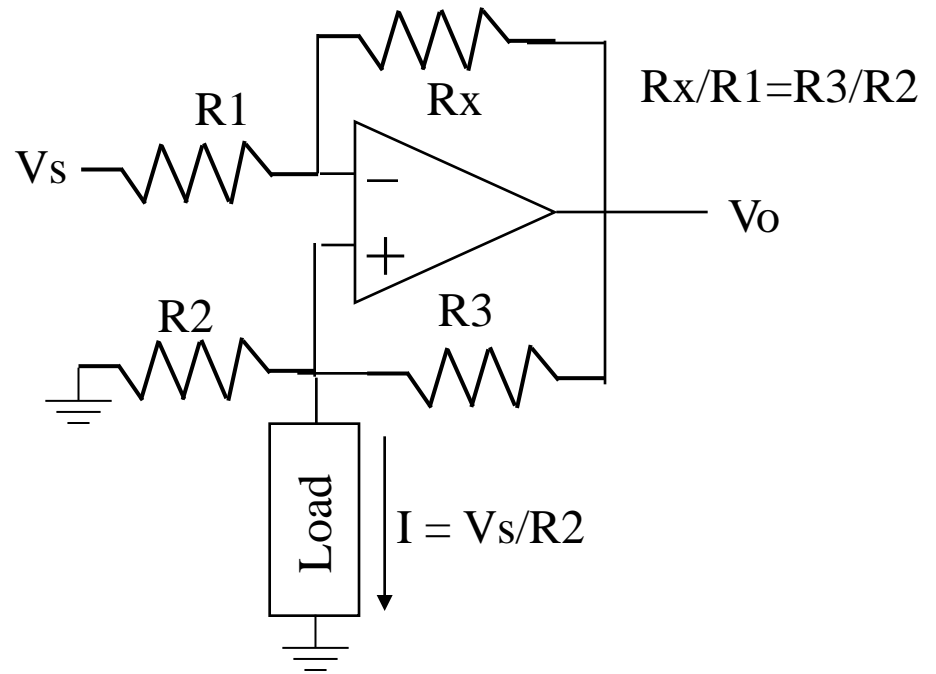


OP AMP CONSTANT CURRENT SOURCE

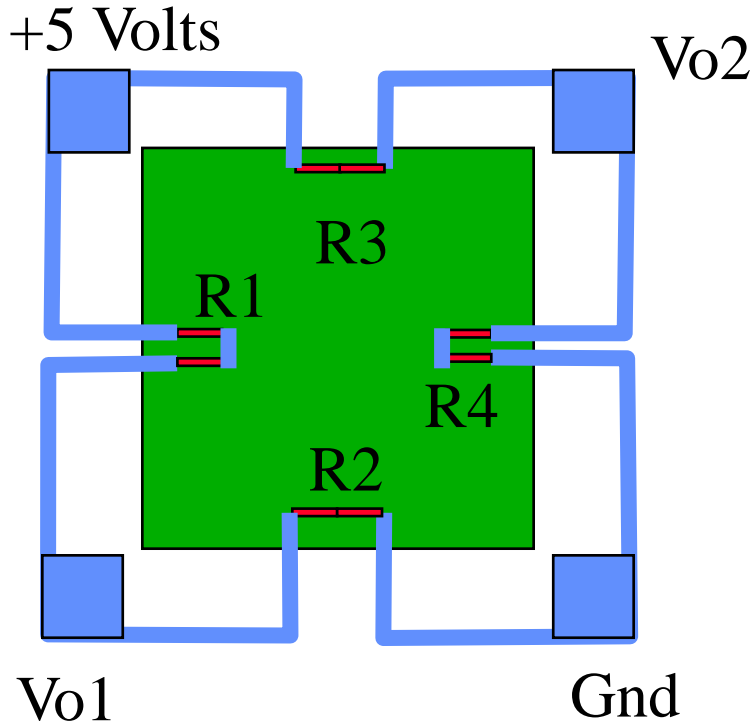
Floating Load



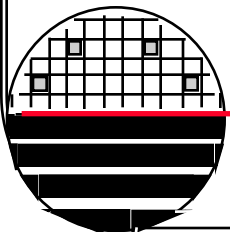
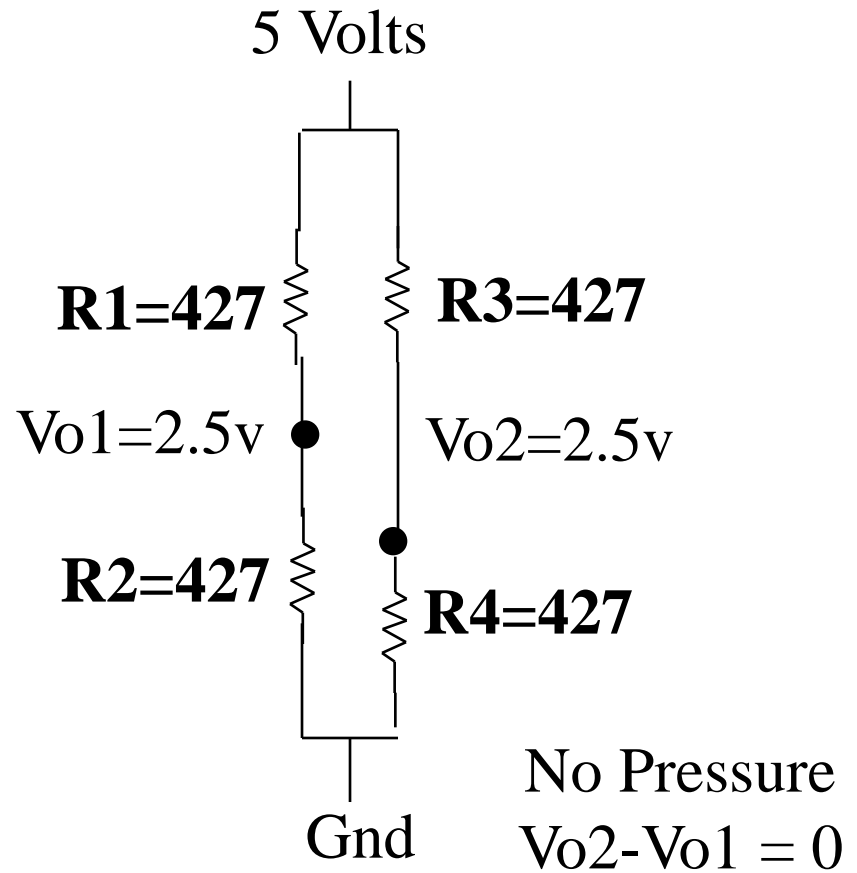
Grounded Load



RESISTIVE PRESSURE SENSOR



Resistors on a Diaphragm



INSTRUMENTATION AMPLIFIER

5 Volts

R1=427.6

R3=426.4

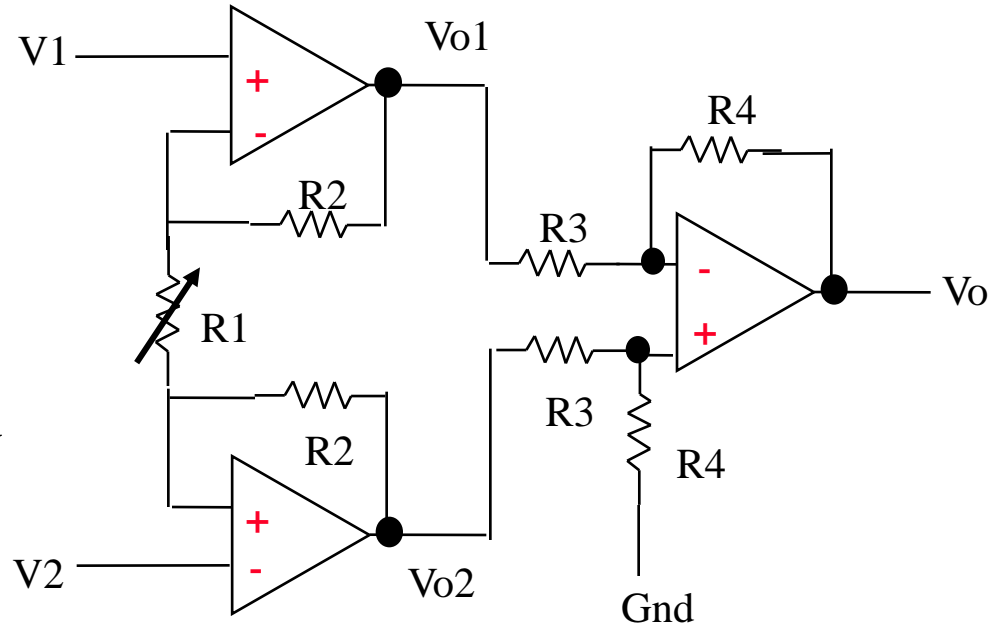
Vo1=2.4965v

Vo2=2.5035v

R2=426.4

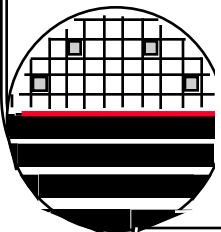
R4=427.6

Gnd

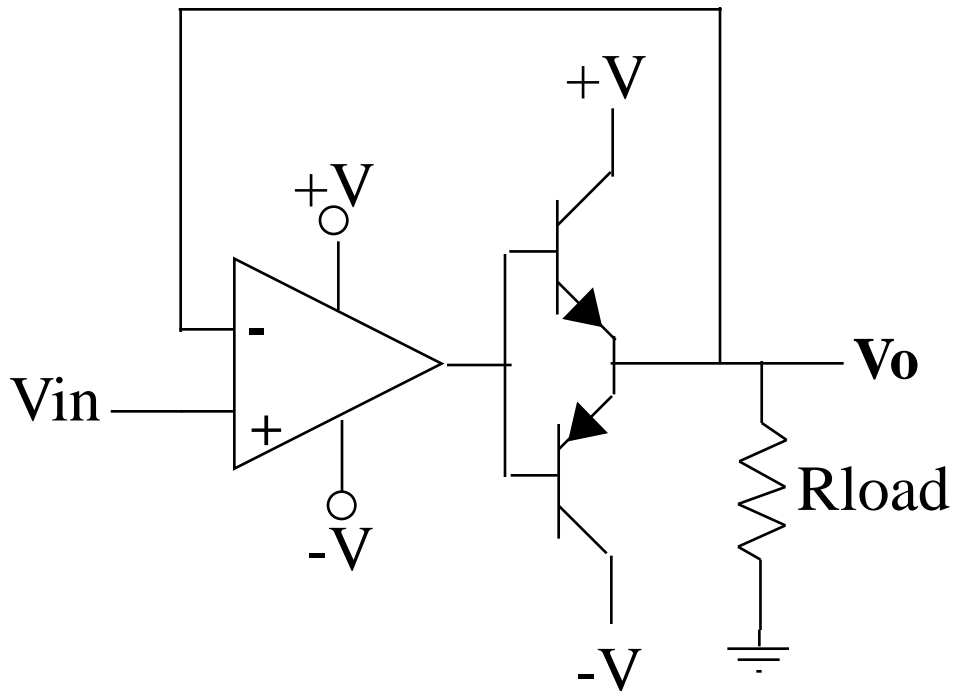


$$V_o = (V_2 - V_1) \frac{R_4}{R_3} \left[1 + \frac{2R_2}{R_1} \right]$$

With Pressure
 Vo2-Vo1 = 0.007v
 = 7 mV

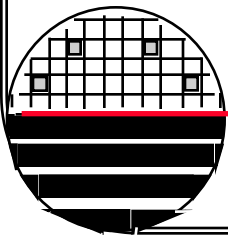


POWER OUTPUT STAGE



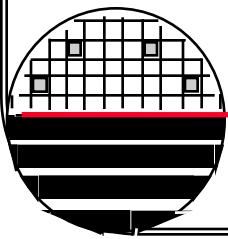
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2. “Active Filter Design Using Operational Transconductance Amplifiers: A Tutorial,” Randall L. Geiger and Edgar Sanchez-Sinencio, IEEE Circuits and Devices Magazine, March 1985, pg. 20-32.
3. Microelectronic Circuits, 5th Edition, Sedra and Smith

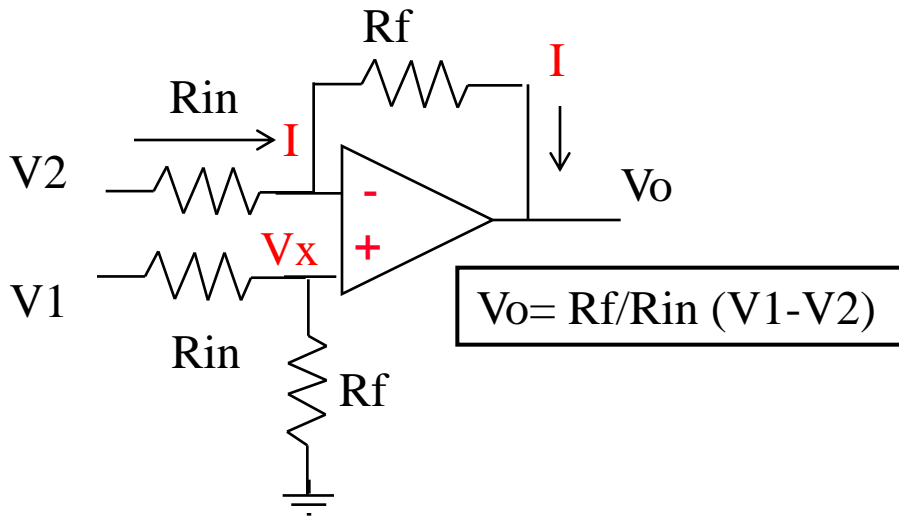


HOMEWORK – BASIC ANALOG CIRCUITS

1. Create one good homework problem and the solution related to the material covered in this document. (for next years students)
2. Design a bistable multivibrator with V_{th} of ± 7.5 volts and frequency of 5 KHz.
3. Design a temperature sensor circuit that will shut down a heater if the temperature exceeds 90°C
4. Design a peak detector that will respond to changes in input in less than one second.
5. Derive the equation for the oscillator on page 15 (multivibrator).
6. Derive the voltage gain equation for the difference amplifier.



DERIVE GAIN EQUATION FOR DIFFERENCE AMP



$$I = (V1 - Vx) / Rin$$

$$Vx = V1 \frac{Rf}{Rf + Rin}$$

$$Vo = -I Rf + Vx$$

Difference Amplifier

